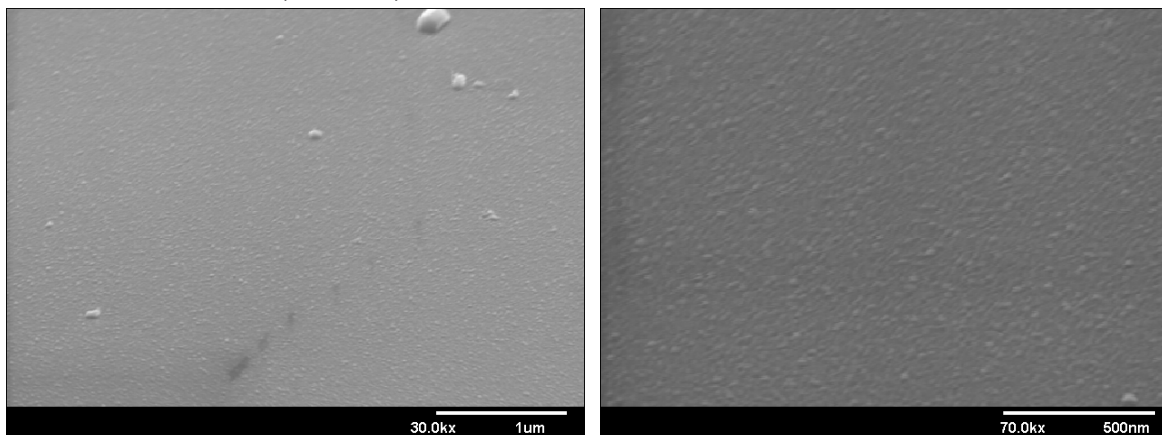
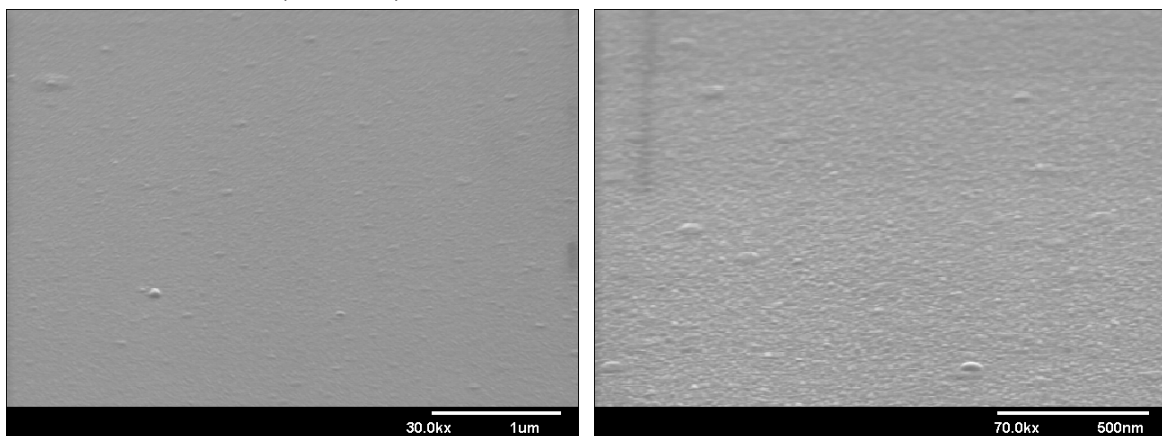


4-6 相同製程前處理之 SEM&AFM 圖面

A1、550°C H₂:100 (Ni 1 nm)



A2、550°C H₂:100 (Ni 5 nm)



A3、550°C H₂:100 (Ni 7 nm)

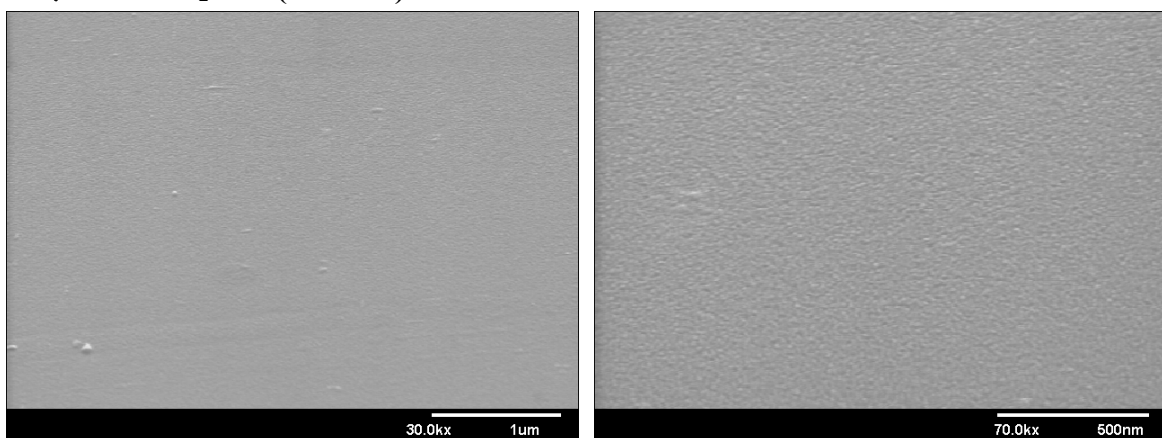
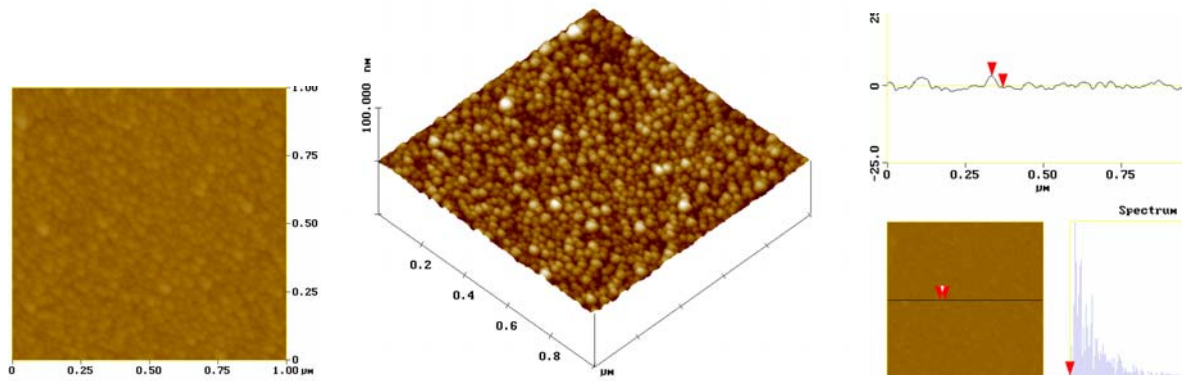
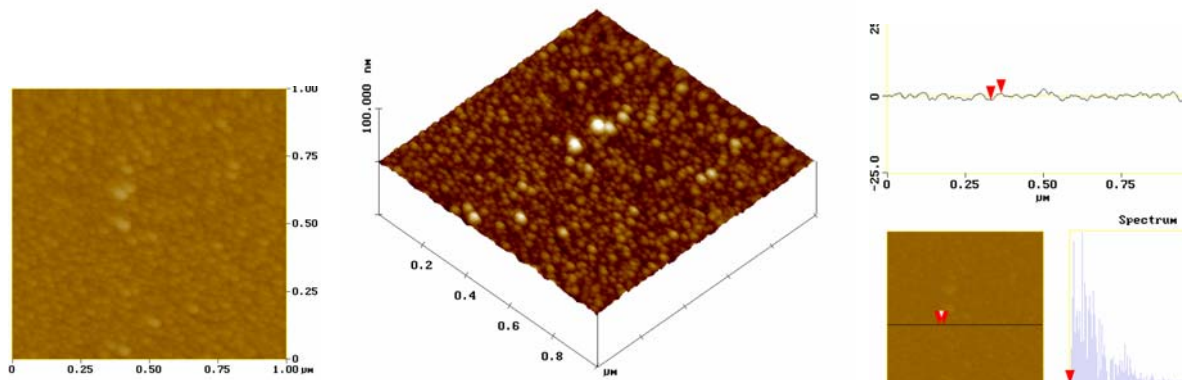


圖 4-6 製程 A 無緩衝層試件(1、2、3) SEM 圖面(30、70 kx)

A1、550°C H₂:100 (Ni 1 nm) ; Rms 0.866 nm



A2、550°C H₂:100 (Ni 5 nm) ; Rms 0.904 nm



A3、550°C H₂:100 (Ni 7 nm) ; Rms 0.700 nm

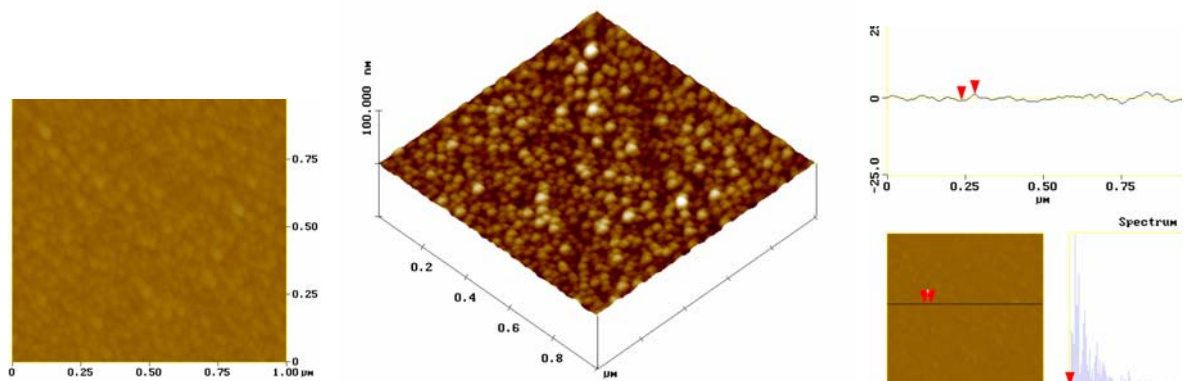
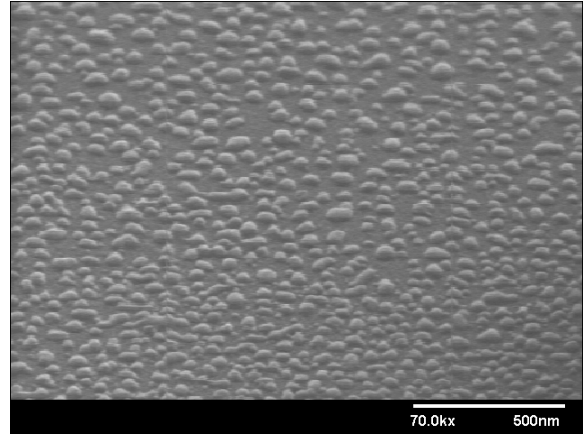
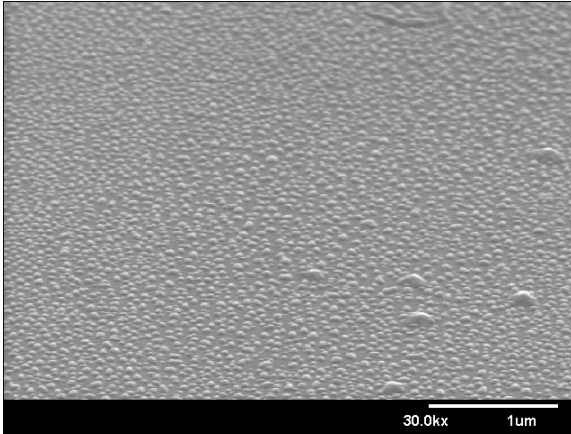
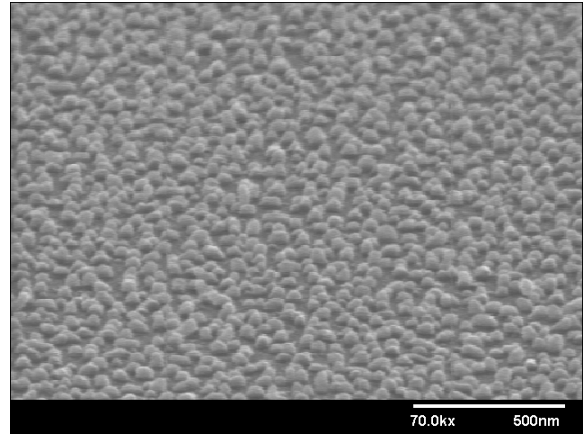
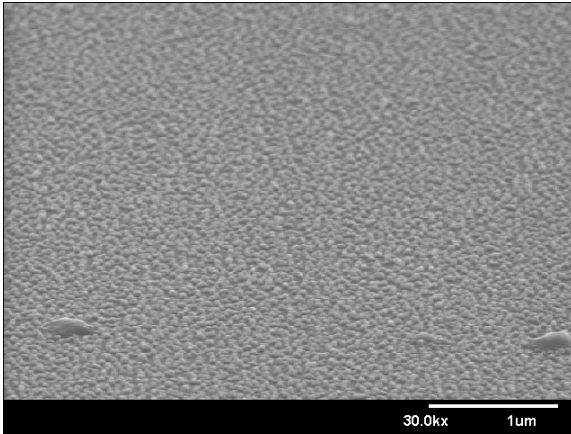


圖 4-7 製程 A 無緩衝層試件(1、2、3)AFM 圖面

B1、550°C H₂:200 (Ni 1 nm)



B2、550°C H₂:200 (Ni 5 nm)



B3、550°C H₂:200 (Ni 7 nm)

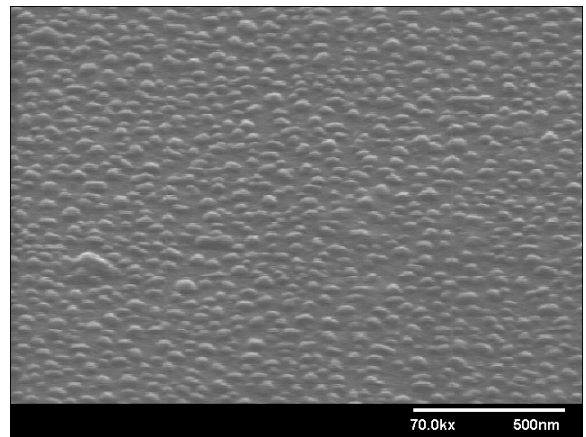
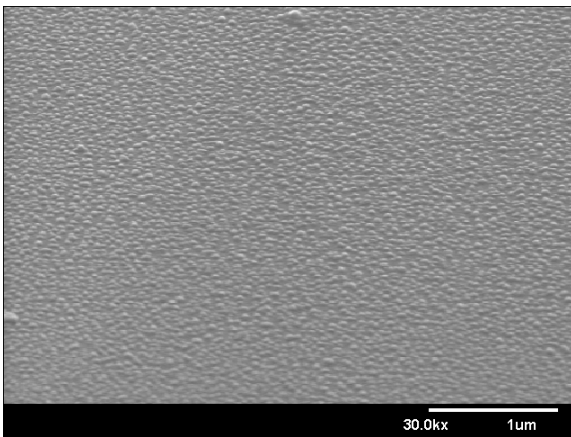
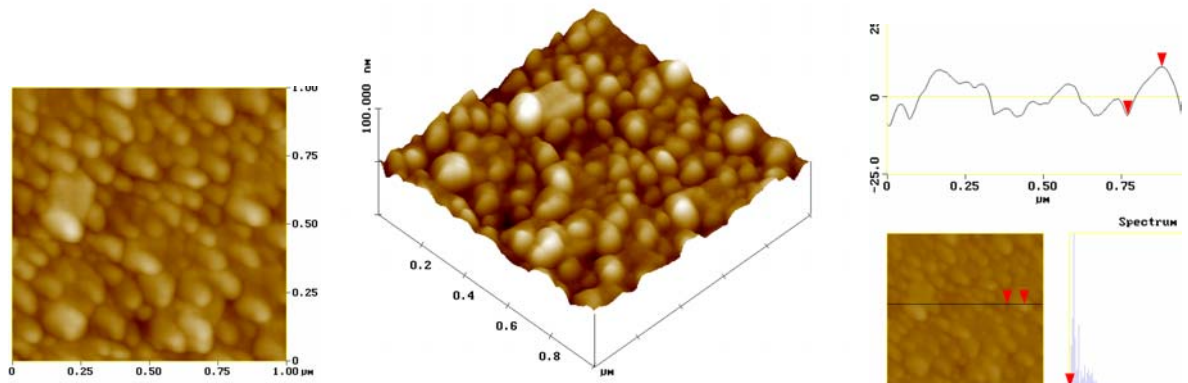
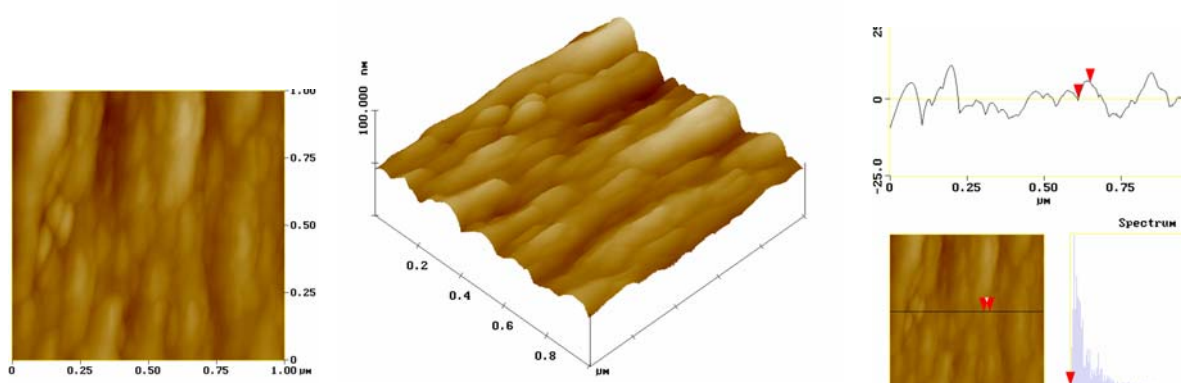


圖 4-8 製程 B 無緩衝層試件(1、2、3) SEM 圖面(30、70 kx)

B1、550°C H₂:200 (Ni 1 nm) ; Rms 3.433 nm



B2、550°C H₂:200 (Ni 5 nm) ; Rms 5.438 nm



B3、550°C H₂:200 (Ni 7 nm) ; Rms 3.274 nm

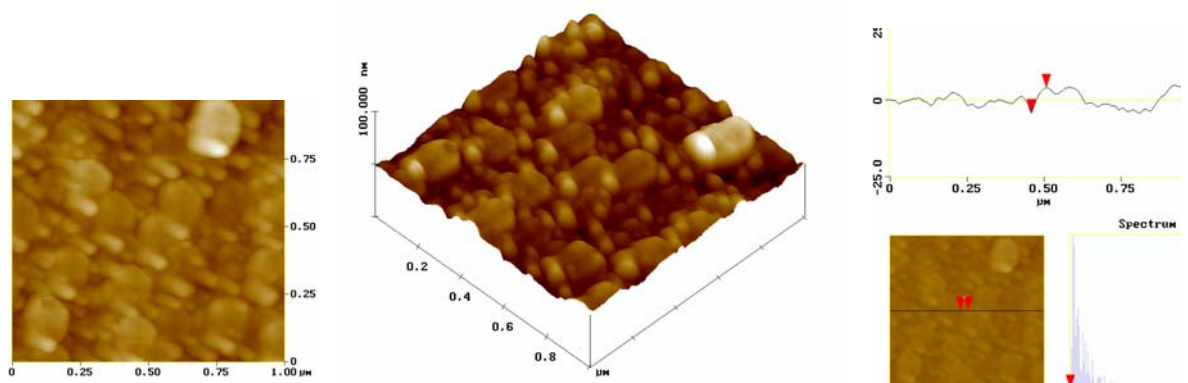


圖 4-9 製程 B 無緩衝層試件(1、2、3) AFM 圖面